

High Gain Darlington Output Optocouplers

Technical Data

4N45 4N46

Features

- **High Current Transfer Ratio—1500% Typical**
- **Low Input Current Requirement—0.5 mA**
- **Performance Guaranteed over 0°C to 70°C Temperature Range**
- **Internal Base-Emitter Resistor Minimizes Output Leakage**
- **Gain-Bandwidth Adjustment Pin**
- **Safety Approval**
UL Recognized -2500 V rms for 1 Minute
CSA Approved

Applications

- **Telephone Ring Detector**
- **Digital Logic Ground Isolation**
- **Low Input Current Line Receiver**
- **Line Voltage Status Indicator—Low Input Power Dissipation**
- **Logic to Reed Relay Interface**
- **Level Shifting**
- **Interface Between Logic Families**

Description

The 4N45/46 optocouplers contain a GaAsP light emitting diode optically coupled to a high gain photodetector IC.

The excellent performance over temperature results from the inclusion of an integrated emitter-base bypass resistor which shunts photodiode and first stage leakage currents as well as bleeding off excess base drive to ground. External access to the second stage base provides the capability for better noise rejection than a conventional photodarlington detector. An external resistor or capacitor at the base can be added to make a gain-bandwidth or input current threshold adjustment. The base lead can also be used for feedback.

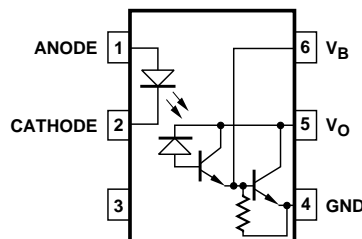
The high current transfer ratio at very low input currents permits circuit designs in which adequate margin can be allowed for the effects of optical coupling variations.

The 4N46 has a 350% minimum CTR at an input current of only 0.5 mA making it ideal for use in low input current applications such as MOS, CMOS and low power logic interfacing. Compatibility with high voltage CMOS logic systems is assured by the 20 V minimum breakdown voltage of the output transistor and by the guaranteed maximum output leakage (I_{OH}) at 18 V.

The 4N45 has a 250% minimum CTR at 1.0 mA input current and a 7 V minimum breakdown voltage rating.

Selection for lower input current down to 250 μ A is available upon request.

Functional Diagram



TRUTH TABLE
(POSITIVE LOGIC)

LED	OUTPUT
ON	L
OFF	H

*JEDEC Registered Data
**JEDEC Registered up to 70°C.

CAUTION: It is advised that normal static precautions be taken in handling and assembly of this component to prevent damage and/or degradation which may be induced by ESD.

Ordering Information

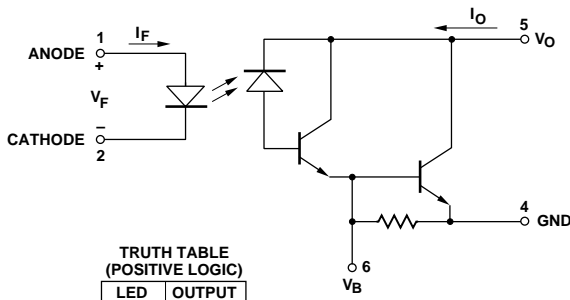
Specify part number followed by Option Number (if desired).

4N45#XXX

- 300 = Gull Wing Surface Mount Lead Option
- 500 = Tape/Reel Package Option (1 K min)

Option data sheets available. Contact your Agilent sales representative or authorized distributor for information.

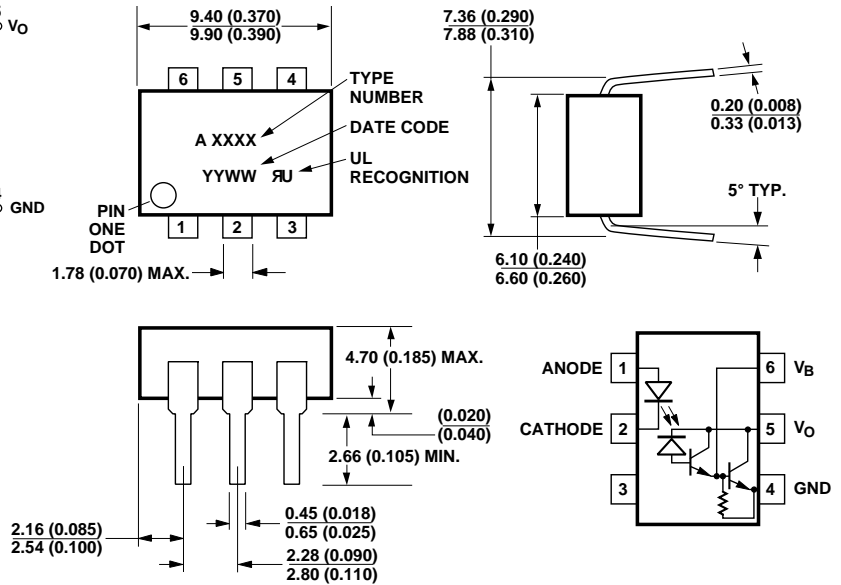
Schematic



TRUTH TABLE
(POSITIVE LOGIC)

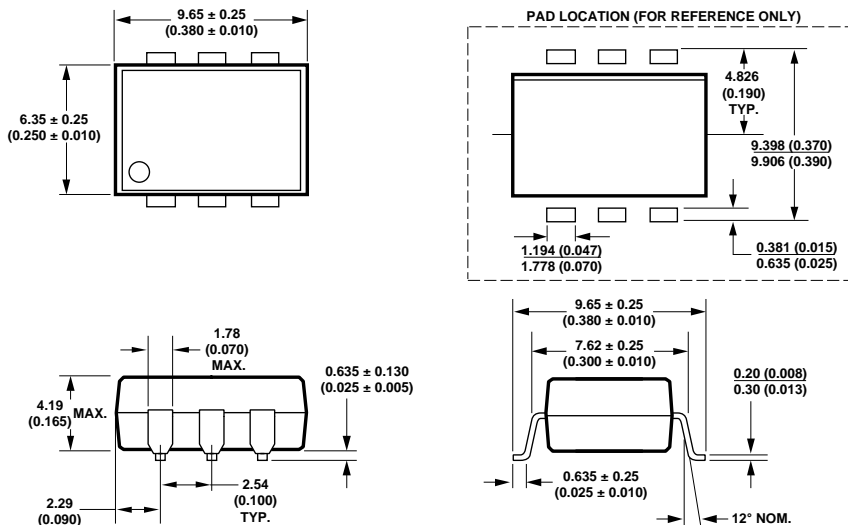
LED	OUTPUT
ON	L
OFF	H

Outline Drawing



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Outline Drawing – Option 300



Thermal Profile (Option #300)

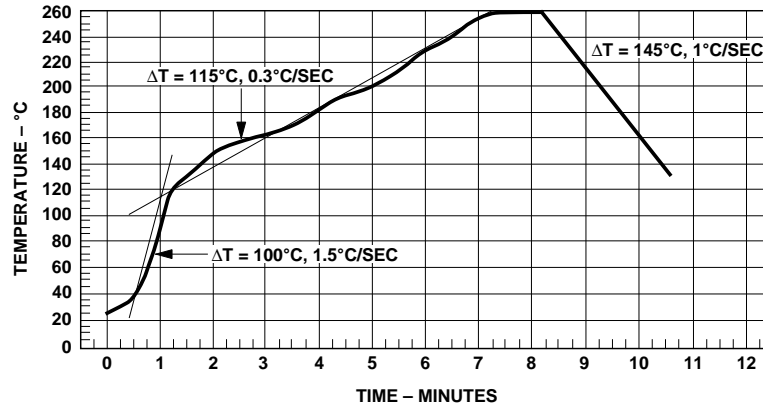


Figure 1. Maximum Solder Reflow Thermal Profile.
(Note: Use of non-chlorine activated fluxes is recommended.)

Regulatory Information

The 4N45 and 4N46 have been approved by the following regulatory organizations:

UL

Recognized under UL 1577, Component Recognition Program, File E55361.

CSA

Approved under CSA Component Acceptance Notice #5, File CA 88324.

Insulation and Safety Related Specifications

Parameter	Symbol	Value	Units	Conditions
Min. External Air Gap (External Clearance)	L(IO1)	7.1	mm	Measured from input terminals to output terminals, shortest distance through air
Min. External Tracking Path (External Creepage)	L(IO2)	7.4	mm	Measured from input terminals to output terminals, shortest distance path along body
Min. Internal Plastic Gap (Internal Clearance)		0.08	mm	Through insulation distance, conductor to conductor, usually the direct distance between the photoemitter and photodetector inside the optocoupler cavity
Tracking Resistance (Comparative Tracking Index)	CTI	200	Volts	DIN IEC 112/VDE 0303 PART 1
Isolation Group		IIIa		Material Group (DIN VDE 0110, 1/89, Table 1)

Option 300 – surface mount classification is Class A in accordance with CECC 00802.

Absolute Maximum Ratings

Storage Temperature, T_S	-55°C to +125°C
Operating Temperature, T_A	-40°C to +85°C
Lead Solder Temperature, max	260°C for 10 s (1.6 mm below seating plane)
Average Input Current, I_F	20 mA ^[1]
Peak Input Current, I_F	40 mA (50% duty cycle, 1 ms pulse width)
Peak Transient Input Current, I_F	1.0 A ($\leq 1 \mu\text{s}$ pulse width, 300 pps)
Reverse Input Voltage, V_R	5 V
Input Power Dissipation, P_I	35 mW ^[2]
Output Current, I_O (Pin 5)	60 mA ^[3]
Emitter-Base Reverse Voltage (Pins 4-6)	0.5 V
Output Voltage, V_O (Pin 5-4)	
4N45	-0.5 to 7 V
4N46	-0.5 to 20 V
Output Power Dissipation	100 mW ^[4]
Infrared and Vapor Phase Reflow Temperature (Option #300)	see Fig. 1, Thermal Profile

Recommended Operating Conditions

Parameter	Symbol	Min.	Max.	Units
Output Voltage (4N46)	V_O	4.5	20	V
Output Voltage (4N45)		4.5	7	V
Input Current (High)	$I_{F(ON)}$	0.5	10	mA
Input Voltage (Low)	$V_{F(OFF)}$	0	0.8	V
Operating Temperature	T_A	0	70	°C

DC Electrical Specifications

Over recommended temperature ($T_A = 0^\circ\text{C}$ to 70°C), unless otherwise specified.

Parameter	Device	Symbol	Min.	Typ.*	Max.	Units	Test Conditions	Fig.	Note
Current Transfer Ratio	4N46	CTR	350*	1500	3200	%	$I_F = 0.5\text{ mA}, V_O = 1.0\text{ V}$	3, 4, 5, 11, 12	5, 6, 8
			500*	1500	2000		$I_F = 1.0\text{ mA}, V_O = 1.0\text{ V}$		
			200*	600	1000		$I_F = 10\text{ mA}, V_O = 1.2\text{ V}$		
	4N45		250*	1200	2000	%	$I_F = 1.0\text{ mA}, V_O = 1.0\text{ V}$		
			200*	500	1000		$I_F = 10\text{ mA}, V_O = 1.2\text{ V}$		
Logic Low Output Voltage	4N46	V_{OL}		0.90	1.0	V	$I_F = 0.5\text{ mA}, I_{OL} = 1.75\text{ mA}$	3	6
				0.92	1.0		$I_F = 1.0\text{ mA}, I_{OL} = 5.0\text{ mA}$		
	4N45			0.90	1.0	V	$I_F = 1.0\text{ mA}, I_{OL} = 2.5\text{ mA}$		
				0.95	1.2		$I_F = 10\text{ mA}, I_{OL} = 20\text{ mA}$		
Logic High Output Current	4N46	I_{OH}^*		0.001	100	μA	$I_F = 0\text{ mA}, V_O = 18\text{ V}$		6
	4N45			0.001	250		$I_F = 0\text{ mA}, V_O = 5\text{ V}$		
Input Forward Voltage		V_F		1.4	1.7*	V	$T_A = 25^\circ\text{C}$ $I_F = 1.0\text{ mA}$	2	
				1.75					
Temperature Coefficient of Forward Voltage		$\frac{\Delta V_F}{\Delta T_A}$		-1.8		mV/°C	$I_F = 1.0\text{ mA}$		
Input Reverse Breakdown Voltage		BV_R^*	5			V	$I_R = 10\text{ }\mu\text{A}$		
Input Capacitance		C_{IN}		60		pF	$f = 1\text{ MHz}, V_F = 0$		

Switching Specifications

(Over recommended temperature $T_A = 0^\circ\text{C}$ to 70°C unless otherwise specified. $V_{CC} = 5.0\text{ V}$.)

Parameter	Symbol	Min.	Typ.*	Max.	Units	Test Conditions	Fig.	Note
Propagation Delay Time to Logic Low at Output	t_{PHL}		80		μs	$T_A = 25^\circ\text{C}$ $I_F = 0.5\text{ mA}$	6, 7, 8, 9, 11, 13	6, 8
			5	50*		$T_A = 25^\circ\text{C}$ $I_F = 10\text{ mA}$		
			60			$R_L = 2.2\text{ k}\Omega$		
Propagation Delay Time to Logic High at Output	t_{PLH}		1500		μs	$T_A = 25^\circ\text{C}$ $I_F = 10\text{ mA}$	6, 7, 8, 9, 11, 13	6, 8
			150	500*		$T_A = 25^\circ\text{C}$ $I_F = 10\text{ mA}$		
			600			$R_L = 220\text{ k}\Omega$		
Common Mode Transient Immunity at High Output Level	$ CM_H $		500		V/ μs	$I_F = 0\text{ mA}, R_L = 10\text{ k}\Omega$ $ V_{CM} = 10\text{ V}_{P-P}$	10	9
Common Mode Transient Immunity at Low Output Level	$ CM_L $		500		V/ μs	$I_F = 1.0\text{ mA}, R_L = 10\text{ k}\Omega$ $ V_{CM} = 10\text{ V}_{P-P}$	10	9

*JEDEC Registered Data.

**All typicals at $T_A = 25^\circ\text{C}$, unless otherwise noted.

Package Characteristics

For $0^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$, unless otherwise specified. All typicals at $T_A = 25^{\circ}\text{C}$.

Parameter	Symbol	Min.	Typ.	Max.	Units	Test Conditions	Fig.	Notes
Input-Output Momentary Withstand Voltage*	V_{ISO}	2500			V rms	$RH \leq 50\%$, $t = 1$ min, $T_A = 25^{\circ}\text{C}$		7, 10
Resistance, Input-Output	R_{I-O}		10^{12}		Ω	$V_{I-O} = 500$ Vdc		7
Capacitance, Input-Output	C_{I-O}		0.6		pF	$f = 1$ MHz		7

*The Input-Output Momentary Withstand Voltage is a dielectric voltage rating that should not be interpreted as an input-output continuous voltage rating. For the continuous voltage rating refer to the VDE 0884 Insulation Characteristics Table (if applicable), your equipment level safety specification, or Agilent Application Note 1074, "Optocoupler Input-Output Endurance Voltage."

Notes:

- Derate linearly above 50°C free-air temperature at a rate of 0.4 mA/ $^{\circ}\text{C}$.
- Derate linearly above 50°C free-air temperature at a rate of 0.7 mW/ $^{\circ}\text{C}$.
- Derate linearly above 25°C free-air temperature at a rate of 0.8 mA/ $^{\circ}\text{C}$.
- Derate linearly above 25°C free-air temperature at a rate of 1.5 mW/ $^{\circ}\text{C}$.
- DC CURRENT TRANSFER RATIO is defined as the ratio of output collector current, I_O , to the forward LED input current, I_F , times 100%.
- Pin 6 Open.
- Device considered a two-terminal device: Pins 1, 2, 3 shorted together and Pins 4, 5, and 6 shorted together.
- Use of a resistor between pin 4 and 6 will decrease gain and delay time. (See Figures 11, 12, and 13.)
- Common mode transient immunity in Logic High level is the maximum tolerable (positive) dV_{cm}/dt on the leading edge of the common mode pulse, V_{CM} , to assure that the output will remain in a Logic High state (i.e., $V_O > 2.5$ V). Common mode transient immunity in Logic Low level is the maximum tolerable (negative) dV_{cm}/dt on the trailing edge of the common mode pulse signal, V_{cm} , to assure that the output will remain in a Logic Low state (i.e., $V_O < 2.5$ V).
- In accordance with UL 1577, each optocoupler is proof tested by applying an insulation test voltage ≥ 3000 V rms for 1 second (leakage detection current limit, $I_{I-O} \leq 5$ μA).

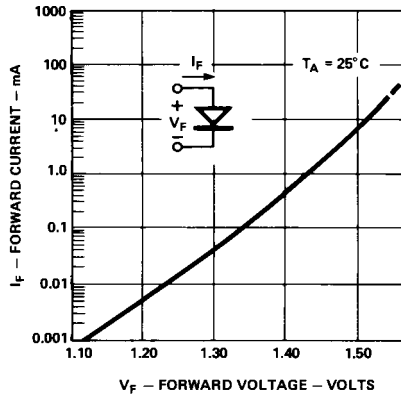


Figure 2. Input Diode Forward Current vs. Forward Voltage.

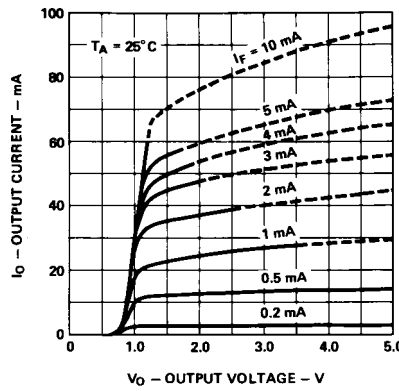


Figure 3. Typical DC Transfer Characteristics.

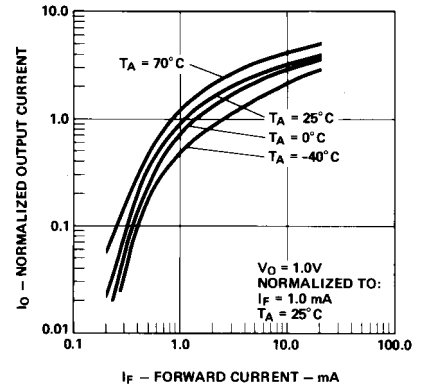


Figure 4. Output Current vs. Input Current.

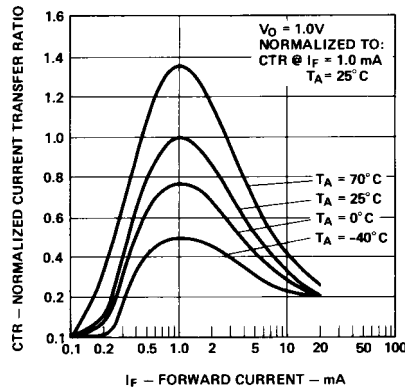


Figure 5. Current Transfer Ratio vs. Input Current.

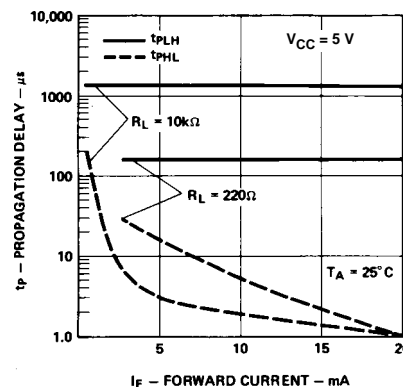


Figure 6. Propagation Delay vs. Forward Current.

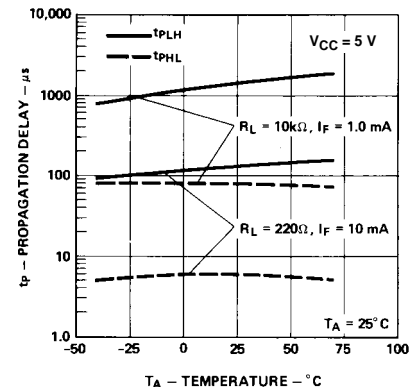


Figure 7. Propagation Delay vs. Temperature.

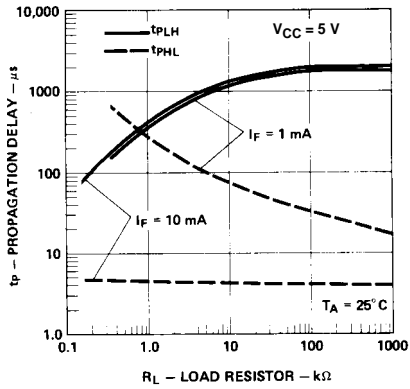


Figure 8. Propagation Delay vs. Load Resistor.



Figure 9. Switching Test Circuit.

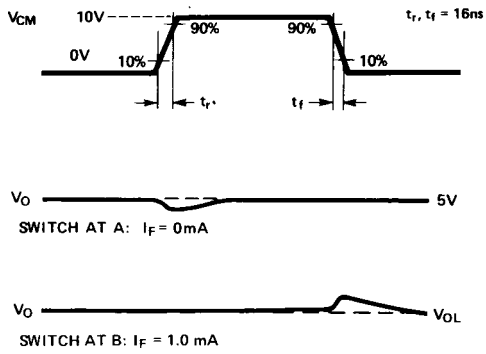


Figure 10. Test Circuit for Transient Immunity and Typical Waveforms.

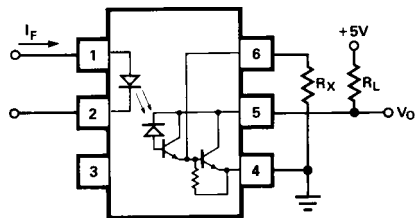


Figure 11. External Base Resistor, R_X .

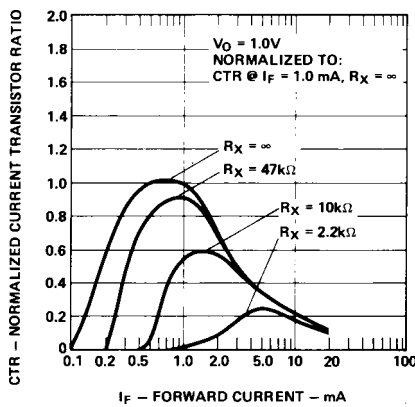


Figure 12. Effect of R_X On Current Transfer Ratio.

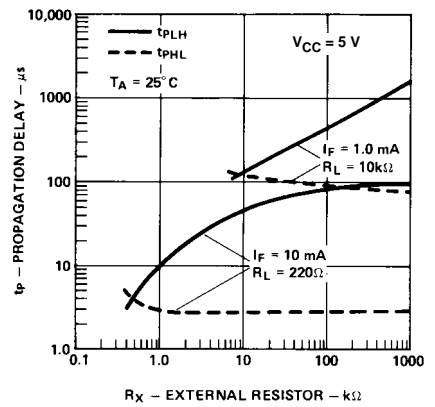
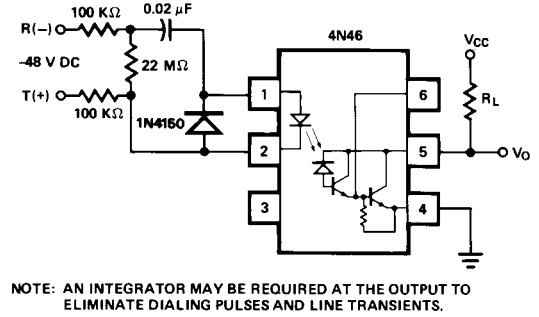
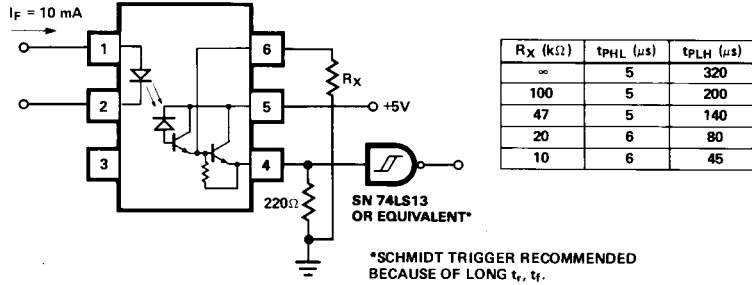
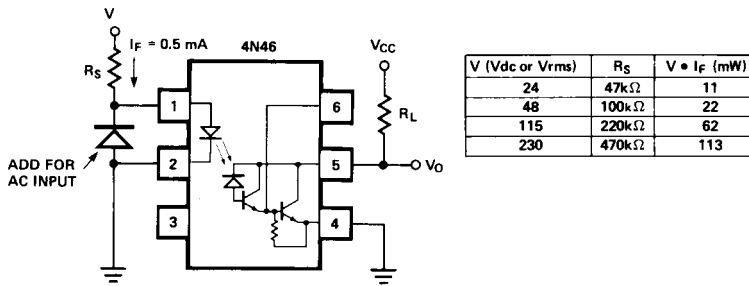


Figure 13. Effect of R_X On Propagation Delay.

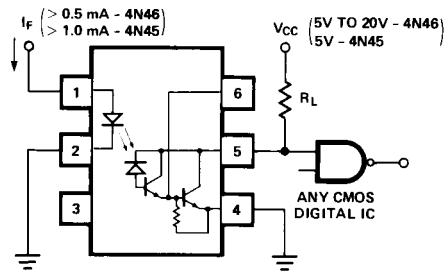
Applications



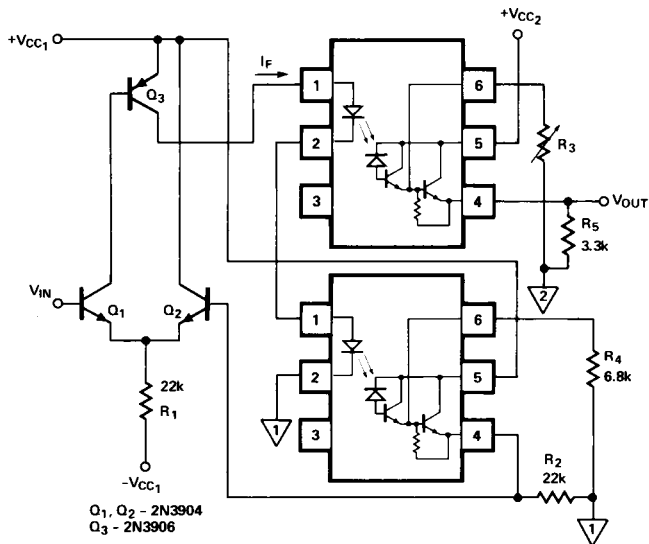
TTL Interface



Telephone Ring Detector



Line Voltage Monitor



CMOS Interface

CHARACTERISTICS

R_{IN} ≈ 30MΩ, R_{OUT} ≈ 50Ω
V_{IN(MAX.)} = V_{CC1} - 1V, LINEARITY BETTER THAN 5%

DESIGN COMMENTS

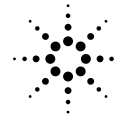
R₁ - NOT CRITICAL ($\ll \frac{V_{IN(MAX.)} - (-V_{CC1}) - V_{BE}}{I_F(MAX.)}$)_{HFE} Q₃
R₂ - NOT CRITICAL (OMIT IF 0.2 TO 0.3V OFFSET IS TOLERABLE)

R₄ > $\frac{V_{IN(MAX.)} + V_{BE}}{1 \text{ mA}}$

R₅ > $\frac{V_{IN(MAX.)}}{2.5 \text{ mA}}$

NOTE: ADJUST R₃ SO V_{OUT} = V_{IN} AT V_{IN} = $\frac{V_{IN(MAX.)}}{2}$

Analog Signal Isolation



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